

**METHOD OF MANUFACTURING A MICROELECTRONIC DEVICE WITH
ELECTRODE PERTURBING SILL**

ABSTRACT

[0045] A method of manufacturing a microelectronic device. The method includes providing a substrate and forming a patterned feature located over the substrate and a plurality of doped regions. The patterned feature also comprises at least one electrode, wherein the electrode is proximate a plurality of doped layers. The method further includes forming a sill located within the electrode, wherein the sill comprising at least one impurity and adapted for modifying an electrical property of at least one member adjacent the electrode.